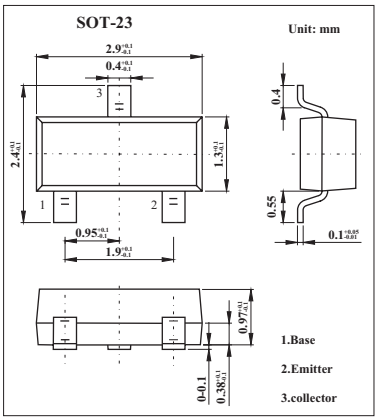
Small Signal Transistor

FMMT2484



■ Features

● 60 Volt V_{CEO}.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Peak collector current	I_{CM}	200	mA
Collector current	I_C	50	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	6			V
Collector cutoff current	I_{CBO}	V_{CB}=45V,I_E=0			10	nA
		V_{CB}=45V,Tam$_B$=150℃			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			10	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=1A,I_B=100μA			0.35	V
Base-emitter voltage *	V_{BE}	I_C=1A,V_{CE}=5V			0.95	V
DC current gain *	h_{FE}	I_C=10μA,V_{CE}=5V	100		500	
Output capacitance	C_{obo}	V_{CB}=5V,f=140KHz			6	pF
Input capacitance	C_{ibo}	V_{BE}=0.5V,f=140KHz			6	pF
Output capacitance	NF	I_C=200μA, V_{CE}=5V, R_g=2kΩ f=1kHz, f=200Hz			3	dB
		I_C=200μA, V_{CE}=5V, R_g=2kΩ f=30Hz to 15kHz at -3dB points			3	dB

* Pulse test: tp ⩽ 300μs; d ⩽ 0.02.

■ Marking

Marking	4G